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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

### Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I <sup>2</sup> C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	17
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	-
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	24-VQFN Exposed Pad
Supplier Device Package	24-QFN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32zg108f32-qfn24t

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# **2 System Summary**

# **2.1 System Introduction**

The EFM32 MCUs are the world's most energy friendly microcontrollers. With a unique combination of the powerful 32-bit ARM Cortex-M0+, innovative low energy techniques, short wake-up time from energy saving modes, and a wide selection of peripherals, the EFM32ZG microcontroller is well suited for any battery operated application as well as other systems requiring high performance and low-energy consumption. This section gives a short introduction to each of the modules in general terms and also shows a summary of the configuration for the EFM32ZG108 devices. For a complete feature set and indepth information on the modules, the reader is referred to the *EFM32ZG Reference Manual*.

A block diagram of the EFM32ZG108 is shown in Figure 2.1 (p. 3) .



### Figure 2.1. Block Diagram

### 2.1.1 ARM Cortex-M0+ Core

The ARM Cortex-M0+ includes a 32-bit RISC processor which can achieve as much as 0.9 Dhrystone MIPS/MHz. A Wake-up Interrupt Controller handling interrupts triggered while the CPU is asleep is included as well. The EFM32 implementation of the Cortex-M0+ is described in detail in *ARM Cortex-M0+ Devices Generic User Guide*.

# 2.1.2 Debug Interface (DBG)

This device includes hardware debug support through a 2-pin serial-wire debug interface .

### 2.1.3 Memory System Controller (MSC)

The Memory System Controller (MSC) is the program memory unit of the EFM32ZG microcontroller. The flash memory is readable and writable from both the Cortex-M0+ and DMA. The flash memory is divided into two blocks; the main block and the information block. Program code is normally written to the main block. Additionally, the information block is available for special user data and flash lock bits. There is also a read-only page in the information block containing system and device calibration data. Read and write operations are supported in the energy modes EM0 and EM1.

### 2.1.12 Pre-Programmed UART Bootloader

The bootloader presented in application note AN0003 is pre-programmed in the device at factory. Autobaud and destructive write are supported. The autobaud feature, interface and commands are described further in the application note.

# 2.1.13 Low Energy Universal Asynchronous Receiver/Transmitter (LEUART)

The unique LEUART<sup>TM</sup>, the Low Energy UART, is a UART that allows two-way UART communication on a strict power budget. Only a 32.768 kHz clock is needed to allow UART communication up to 9600 baud/s. The LEUART includes all necessary hardware support to make asynchronous serial communication possible with minimum of software intervention and energy consumption.

### 2.1.14 Timer/Counter (TIMER)

The 16-bit general purpose Timer has 3 compare/capture channels for input capture and compare/Pulse-Width Modulation (PWM) output.

### 2.1.15 Real Time Counter (RTC)

The Real Time Counter (RTC) contains a 24-bit counter and is clocked either by a 32.768 kHz crystal oscillator, or a 32.768 kHz RC oscillator. In addition to energy modes EM0 and EM1, the RTC is also available in EM2. This makes it ideal for keeping track of time since the RTC is enabled in EM2 where most of the device is powered down.

### 2.1.16 Pulse Counter (PCNT)

The Pulse Counter (PCNT) can be used for counting pulses on a single input or to decode quadrature encoded inputs. It runs off either the internal LFACLK or the PCNTn\_S0IN pin as external clock source. The module may operate in energy mode EM0 - EM3.

### 2.1.17 Analog Comparator (ACMP)

The Analog Comparator is used to compare the voltage of two analog inputs, with a digital output indicating which input voltage is higher. Inputs can either be one of the selectable internal references or from external pins. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

### 2.1.18 Voltage Comparator (VCMP)

The Voltage Supply Comparator is used to monitor the supply voltage from software. An interrupt can be generated when the supply falls below or rises above a programmable threshold. Response time and thereby also the current consumption can be configured by altering the current supply to the comparator.

### 2.1.19 General Purpose Input/Output (GPIO)

In the EFM32ZG108, there are 17 General Purpose Input/Output (GPIO) pins, which are divided into ports with up to 16 pins each. These pins can individually be configured as either an output or input. More advanced configurations like open-drain, filtering and drive strength can also be configured individually for the pins. The GPIO pins can also be overridden by peripheral pin connections, like Timer PWM outputs or USART communication, which can be routed to several locations on the device. The GPIO supports up to 11 asynchronous external pin interrupts, which enables interrupts from any pin on the device. Also, the input value of a pin can be routed through the Peripheral Reflex System to other peripherals.

# 2.2 Configuration Summary

The features of the EFM32ZG108 is a subset of the feature set described in the EFM32ZG Reference Manual. Table 2.1 (p. 6) describes device specific implementation of the features.

### Table 2.1. Configuration Summary

Module	Configuration	Pin Connections
Cortex-M0+	Full configuration	NA
DBG	Full configuration	DBG_SWCLK, DBG_SWDIO,
MSC	Full configuration	NA
DMA	Full configuration	NA
RMU	Full configuration	NA
EMU	Full configuration	NA
СМU	Full configuration	CMU_OUT0, CMU_OUT1
WDOG	Full configuration	NA
PRS	Full configuration	NA
I2C0	Full configuration	12C0_SDA, 12C0_SCL
USART1	Full configuration with I2S and IrDA	US1_TX, US1_RX, US1_CLK, US1_CS
LEUART0	Full configuration	LEU0_TX, LEU0_RX
TIMER0	Full configuration	TIM0_CC[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
RTC	Full configuration	NA
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
ACMP0	Full configuration	ACMP0_CH[1:0], ACMP0_O
VCMP	Full configuration	NA
GPIO	17 pins	Available pins are shown in Table 4.3 (p. 40)

# 2.3 Memory Map

The *EFM32ZG108* memory map is shown in Figure 2.2 (p. 7), with RAM and Flash sizes for the largest memory configuration.

# **3 Electrical Characteristics**

# **3.1 Test Conditions**

### 3.1.1 Typical Values

The typical data are based on  $T_{AMB}=25^{\circ}C$  and  $V_{DD}=3.0$  V, as defined in Table 3.2 (p. 8), by simulation and/or technology characterisation unless otherwise specified.

### 3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 8), by simulation and/or technology characterisation unless otherwise specified.

### **3.2 Absolute Maximum Ratings**

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 8) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 8).

Symbol	Parameter	Condition	Min	Тур	Max	Unit
T <sub>STG</sub>	Storage tempera- ture range		-40		150 <sup>1</sup>	°C
Τ <sub>S</sub>	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	°C
V <sub>DDMAX</sub>	External main sup- ply voltage		0		3.8	V
V <sub>IOPIN</sub>	Voltage on any I/O pin		-0.3		V <sub>DD</sub> +0.3	V

### Table 3.1. Absolute Maximum Ratings

<sup>1</sup>Based on programmed devices tested for 10000 hours at 150°C. Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

# **3.3 General Operating Conditions**

# 3.3.1 General Operating Conditions

### Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Тур	Мах	Unit
T <sub>AMB</sub>	Ambient temperature range	-40		85	°C
V <sub>DDOP</sub>	Operating supply voltage	1.98		3.8	V
f <sub>APB</sub>	Internal APB clock frequency			24	MHz
f <sub>AHB</sub>	Internal AHB clock frequency			24	MHz

# **3.4 Current Consumption**

### Table 3.3. Current Consumption

Symbol	Parameter	Condition	Min	Тур	Max	Unit
		24 MHz HFXO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		115	132	μΑ/ MHz
		24 MHz HFXO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		117	136	μΑ/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		114	128	μΑ/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		116	132	μΑ/ MHz
		14 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		117	131	μΑ/ MHz
I <sub>EMO</sub>	EM0 current. No prescaling. Running prime number cal- culation code from	14 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		118	133	μΑ/ MHz
EMO	Flash. (Production test condition = 14 MHz)	11 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		118	133	μΑ/ MHz
		11 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		120	135	µA/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		124	139	μΑ/ MHz
		6.6 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		125	142	μΑ/ MHz
		1.2 MHz HFRCO, all peripher- al clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		155	177	μΑ/ MHz
		1.2 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		162	181	μΑ/ MHz
		24 MHz HFXO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		48	57	μΑ/ MHz
I <sub>EM1</sub>	EM1 current (Pro-	24 MHz HFXO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		49	59	μΑ/ MHz
	duction test condi- tion = 14 MHz)	21 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =25°C		48	52	μΑ/ MHz
		21 MHz HFRCO, all peripheral clocks disabled, $V_{DD}$ = 3.0 V, $T_{AMB}$ =85°C		49	53	μΑ/ MHz

*Figure 3.5. EM0 Current consumption while executing prime number calculation code from flash with HFRCO running at 6.6 MHz* 



### 3.4.2 EM1 Current Consumption

Figure 3.6. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 24 MHz



Figure 3.7. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 21 MHz



Figure 3.8. EM1 Current consumption with all peripheral clocks disabled and HFRCO running at 14 MHz



### 3.4.5 EM4 Current Consumption





# **3.5 Transition between Energy Modes**

The transition times are measured from the trigger to the first clock edge in the CPU.

Table 3.4. Energy Modes Transitions

Symbol	Parameter	Min	Тур	Max	Unit
t <sub>EM10</sub>	Transition time from EM1 to EM0		0		HF- CORE- CLK cycles
t <sub>EM20</sub>	Transition time from EM2 to EM0		2		μs
t <sub>EM30</sub>	Transition time from EM3 to EM0		2		μs
t <sub>EM40</sub>	Transition time from EM4 to EM0		163		μs

# 3.6 Power Management

The EFM32ZG requires the AVDD\_x, VDD\_DREG and IOVDD\_x pins to be connected together (with optional filter) at the PCB level. For practical schematic recommendations, please see the application note, "AN0002 EFM32 Hardware Design Considerations".

### Table 3.5. Power Management

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V <sub>BODextthr</sub> -	BOD threshold on falling external supply voltage		1.74		1.96	V
V <sub>BODextthr+</sub>	BOD threshold on rising external sup- ply voltage			1.85		V
t <sub>RESET</sub>	Delay from reset is released until program execution starts	Applies to Power-on Reset, Brown-out Reset and pin reset.		163		μs
C <sub>DECOUPLE</sub>	Voltage regulator decoupling capaci- tor.	X5R capacitor recommended. Apply between DECOUPLE pin and GROUND		1		μF

# 3.7 Flash

### Table 3.6. Flash

Symbol	Parameter	Condition	Min	Тур	Max	Unit
EC <sub>FLASH</sub>	Flash erase cycles before failure		20000			cycles
		T <sub>AMB</sub> <150°C	10000			h
RET <sub>FLASH</sub>	Flash data retention	T <sub>AMB</sub> <85°C	10			years
		T <sub>AMB</sub> <70°C	20			years
t <sub>W_PROG</sub>	Word (32-bit) pro- gramming time		20			μs
t <sub>P_ERASE</sub>	Page erase time		20	20.4	20.8	ms
t <sub>D_ERASE</sub>	Device erase time		40	40.8	41.6	ms
I <sub>ERASE</sub>	Erase current				7 <sup>1</sup>	mA
I <sub>WRITE</sub>	Write current				7 <sup>1</sup>	mA
V <sub>FLASH</sub>	Supply voltage dur- ing flash erase and write		1.98		3.8	V

<sup>1</sup>Measured at 25°C

# 3.8 General Purpose Input Output

### Table 3.7. GPIO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
V <sub>IOIL</sub>	Input low voltage				0.30V <sub>DD</sub>	V
V <sub>IOIH</sub>	Input high voltage		0.70V <sub>DD</sub>			V
	V <sub>IOOH</sub> V <sub>IOOH</sub> VIOOH Output high volt- age (Production test condition = 3.0V, DRIVEMODE = STANDARD)	Sourcing 0.1 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.80V <sub>DD</sub>		V
V <sub>IOOH</sub>		Sourcing 0.1 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.90V <sub>DD</sub>		V



Symbol	Parameter	Condition	Min	Тур	Max	Unit
		Sourcing 1 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.85V <sub>DD</sub>		V
		Sourcing 1 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.90V <sub>DD</sub>		V
		Sourcing 6 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.75V <sub>DD</sub>			V
		Sourcing 6 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD	0.85V <sub>DD</sub>			V
		Sourcing 20 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.60V <sub>DD</sub>			V
		Sourcing 20 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH	0.80V <sub>DD</sub>			V
		Sinking 0.1 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.20V <sub>DD</sub>		V
		Sinking 0.1 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOWEST		0.10V <sub>DD</sub>		V
		Sinking 1 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.10V <sub>DD</sub>		V
Maa	Output low voltage (Production test condition = 3.0V,	Sinking 1 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = LOW		0.05V <sub>DD</sub>		V
V <sub>IOOL</sub>	DRIVEMODE = STANDARD)	Sinking 6 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.30V <sub>DD</sub>	V
		Sinking 6 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = STANDARD			0.20V <sub>DD</sub>	V
		Sinking 20 mA, V <sub>DD</sub> =1.98 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.35V <sub>DD</sub>	V
		Sinking 20 mA, V <sub>DD</sub> =3.0 V, GPIO_Px_CTRL DRIVEMODE = HIGH			0.25V <sub>DD</sub>	V
I <sub>IOLEAK</sub>	Input leakage cur- rent	High Impedance IO connected to GROUND or Vdd		±0.1	±100	nA
R <sub>PU</sub>	I/O pin pull-up resis- tor			40		kOhm
R <sub>PD</sub>	I/O pin pull-down re- sistor			40		kOhm
R <sub>IOESD</sub>	Internal ESD series resistor			200		Ohm
t <sub>IOGLITCH</sub>	Pulse width of puls- es to be removed		10		50	ns



### Figure 3.17. Typical High-Level Output Current, 3V Supply Voltage



GPIO\_Px\_CTRL DRIVEMODE = STANDARD





### Figure 3.18. Typical Low-Level Output Current, 3.8V Supply Voltage



GPIO\_Px\_CTRL DRIVEMODE = LOWEST



GPIO\_Px\_CTRL DRIVEMODE = STANDARD



GPIO\_Px\_CTRL DRIVEMODE = LOW



GPIO\_Px\_CTRL DRIVEMODE = HIGH

# 3.9 Oscillators

### 3.9.1 LFXO

### Table 3.8. LFXO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f <sub>LFXO</sub>	Supported nominal crystal frequency			32.768		kHz
ESR <sub>LFXO</sub>	Supported crystal equivalent series re- sistance (ESR)			30	120	kOhm
C <sub>LFXOL</sub>	Supported crystal external load range		5		25	pF
I <sub>LFXO</sub>	Current consump- tion for core and buffer after startup.	ESR=30 kOhm, C <sub>L</sub> =10 pF, LFXOBOOST in CMU_CTRL is 1		190		nA
t <sub>LFXO</sub>	Start- up time.	ESR=30 kOhm, C <sub>L</sub> =10 pF, 40% - 60% duty cycle has been reached, LFXOBOOST in CMU_CTRL is 1		1100		ms

For safe startup of a given crystal, the energyAware Designer in Simplicity Studio contains a tool to help users configure both load capacitance and software settings for using the LFXO. For details regarding the crystal configuration, the reader is referred to application note "AN0016 EFM32 Oscillator Design Consideration".

### 3.9.2 HFXO

### Table 3.9. HFXO

Symbol	Parameter	Condition	Min	Тур	Max	Unit
f <sub>HFXO</sub>	Supported nominal crystal Frequency		4		24	MHz
<b>F0D</b>	Supported crystal	Crystal frequency 24 MHz		30	100	Ohm
ESR <sub>HFXO</sub>	equivalent series re- sistance (ESR)	Crystal frequency 4 MHz		400	1500	Ohm
9 <sub>mHFXO</sub>	The transconduc- tance of the HFXO input transistor at crystal startup	HFXOBOOST in CMU_CTRL equals 0b11	20			mS
C <sub>HFXOL</sub>	Supported crystal external load range		5		25	pF
	Current consump- tion for HFXO after startup	4 MHz: ESR=400 Ohm, C <sub>L</sub> =20 pF, HFXOBOOST in CMU_CTRL equals 0b11		85		μΑ
I <sub>HFXO</sub>		24 MHz: ESR=30 Ohm, $C_L=10 \text{ pF}$ , HFXOBOOST in CMU_CTRL equals 0b11		165		μΑ
t <sub>HFXO</sub>	Startup time	24 MHz: ESR=30 Ohm, $C_L=10 \text{ pF}$ , HFXOBOOST in CMU_CTRL equals 0b11		785		μs



Alternate	LOCATION							
Functionality	0 1 2 3 4 5 6				4	Description		
								USART1 Synchronous mode Master Input / Slave Output (MISO).
US1_TX	PC0		PD7	PD7				USART1 Asynchronous Transmit.Also used as receive input in half duplex communication. USART1 Synchronous mode Master Output / Slave Input (MOSI).

# 4.3 GPIO Pinout Overview

The specific GPIO pins available in *EFM32ZG108* is shown in Table 4.3 (p. 40). Each GPIO port is organized as 16-bit ports indicated by letters A through F, and the individual pin on this port is indicated by a number from 15 down to 0.

### Table 4.3. GPIO Pinout

Port	Pin 15	Pin 14	Pin 13	Pin 12	Pin 11	Pin 10	Pin 9	Pin 8	Pin 7	Pin 6	Pin 5	Pin 4	Pin 3	Pin 2	Pin 1	Pin 0
Port A	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	PA0
Port B	-	PB14	PB13	-	PB11	-	-	PB8	PB7	-	-	-	-	-	-	-
Port C	PC15	PC14	-	-	-	-	-	-	-	-	-	-	-	-	PC1	PC0
Port D	-	-	-	-	-	-	-	-	PD7	PD6	-	-	-	-	-	-
Port E	-	-	PE13	PE12	-	-	-	-	-	-	-	-	-	-	-	-
Port F	-	-	-	-	-	-	-	-	-	-	-	-	-	PF2	PF1	PF0

# 4.4 QFN24 Package

### Figure 4.2. QFN24





### Figure 5.2. QFN24 PCB Solder Mask



### Table 5.2. QFN24 PCB Solder Mask Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Dim. (mm)
а	0.92	е	5.00
b	0.42	f	3.72
с	0.65	g	3.72
d	5.00	-	-



### Figure 5.3. QFN24 PCB Stencil Design



Table 5.3. QFN24 PCB Stencil Design Dimensions (Dimensions in mm)

Symbol	Dim. (mm)	Symbol	Dim. (mm)
а	0.60	е	5.00
b	0.25	х	1.00
с	0.65	У	1.00
d	5.00	Z	0.50

- 1. The drawings are not to scale.
- 2. All dimensions are in millimeters.
- 3. All drawings are subject to change without notice.
- 4. The PCB Land Pattern drawing is in compliance with IPC-7351B.
- 5. Stencil thickness 0.125 mm.
- 6. For detailed pin-positioning, see Figure 4.2 (p. 40).

# **5.2 Soldering Information**

The latest IPC/JEDEC J-STD-020 recommendations for Pb-Free reflow soldering should be followed.

The packages have a Moisture Sensitivity Level rating of 3, please see the latest IPC/JEDEC J-STD-033 standard for MSL description and level 3 bake conditions. Place as many and as small as possible vias underneath each of the solder patches under the ground pad.

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# List of Tables

1.1. Ordering Information	2
2.1. Configuration Summary	6
3.1. Absolute Maximum Ratings	8
3.2. General Operating Conditions	8
3.3. Current Consumption	9
3.4. Energy Modes Transitions	17
3.5. Power Management	
3.6. Flash	18
3.7. GPIO	18
3.8. LFXO	27
3.9. HFXO	
3.10. LFRCO	
3.11. HFRCO	
3.12. AUXHFRCO	
3.13. ULFRCO	-
3.14. ACMP	
3.15. VCMP	
3.16. I2C Standard-mode (Sm)	
3.17. I2C Fast-mode (Fm)	
3.18. I2C Fast-mode Plus (Fm+)	35
3.19. Digital Peripherals	
4.1. Device Pinout	
4.2. Alternate functionality overview	
4.3. GPIO Pinout	
4.4. QFN24 (Dimensions in mm)	
5.1. QFN24 PCB Land Pattern Dimensions (Dimensions in mm)	
5.2. QFN24 PCB Solder Mask Dimensions (Dimensions in mm)	
5.3. QFN24 PCB Stencil Design Dimensions (Dimensions in mm)	44



# List of Equations

3.1. Total ACMP Active Current	. 32
3.2. VCMP Trigger Level as a Function of Level Setting	. 34

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